

1. Description

The AQXX-02HTG Series TVS Diode Array is designed to protect sensitive equipment from damage due to electrostatic discharge (ESD), electrical fast transients (EFT), and lightning induced surges.

3. Features

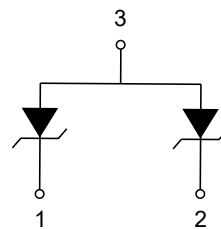
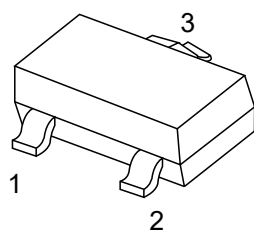
- ESD, IEC 61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC 61000-4-4, 50A (5/50ns)
- Lightning, 33A (8/20 μs as defined in IEC 61000-4-5 2nd edition) for the AQ05
- Working voltages: 5V, 12V, 15V, 24V and 36V

2. Applications

- Industrial Equipment
- Test and Medical Equipment
- Point-of-Sale Terminals
- Motor Controls
- Legacy Ports (RS-232, RS-485)
- Security and Alarm Systems

- ESD, ISO 10605, 330pF 330 Ω , $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- Low clamping voltage
- Low leakage current
- Moisture Sensitivity Level (MSL -1)

4. Pinning information



SOT-23



5. Absolute Maximum Ratings

Parameter	Symbol	Value	Units
Peak Current ($t_p=8/20\mu s$)	P_{PK}	500	W
Junction Temperature	T_{OP}	-40 to 150	°C
Storage Temperature	T_{STOR}	-55 to 150	°C

Notes:

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component.

This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.



6.1AQ05 Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Reverse stand-off voltage	V _{RWM}	I _R =1μA			5	V
Breakdown Voltage	V _{BR}	I _R =1mA	6	7		V
Reverse Leakage Current	I _{LEAK}	V _R =5V			1	μA
Clamp Voltage ¹	V _C	I _{PP} =1A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		8	9.8	V
		I _{PP} =10A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		10.5	13	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Pin 1 or Pin 2 to Pin 3		0.19		Ω
Peak Pulse Current	I _{PP}	t _p =8/20μs			33	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz		290	350	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz		145	180	pF

6.2AQ12 Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Reverse stand-off voltage	V _{RWM}	I _R =1μA			12	V
Breakdown Voltage	V _{BR}	I _R =1mA	13.3	14.2		V
Reverse Leakage Current	I _{LEAK}	V _R =12V			1	μA
Clamp Voltage ¹	V _C	I _{PP} =1A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		16	18.5	V
		I _{PP} =10A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		20	22.5	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Pin 1 or Pin 2 to Pin 3		0.25		Ω
Peak Pulse Current	I _{PP}	t _p =8/20μs			20	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz		110	135	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz		55	85	pF



6.3AQ15 Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Reverse stand-off voltage	V _{RWM}	I _R =1μA			15	V
Breakdown Voltage	V _{BR}	I _R =1mA	16.7	18.5		V
Reverse Leakage Current	I _{LEAK}	V _R =15V			1	μA
Clamp Voltage ¹	V _C	I _{PP} =1A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		20.5	24	V
		I _{PP} =10A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		26.6	30	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Pin 1 or Pin 2 to Pin 3		0.3		Ω
Peak Pulse Current	I _{PP}	t _p =8/20μs			15	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz		85	100	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz		45	75	pF

6.4AQ24 Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Reverse stand-off voltage	V _{RWM}	I _R =1μA			24	V
Breakdown Voltage	V _{BR}	I _R =1mA	26.7	28		V
Reverse Leakage Current	I _{LEAK}	V _R =24V			1	μA
Clamp Voltage ¹	V _C	I _{PP} =1A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		30	36	V
		I _{PP} =5A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		36	42	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Pin 1 or Pin 2 to Pin 3		0.5		Ω
Peak Pulse Current	I _{PP}	t _p =8/20μs			9	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz		60	65	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz		30	50	pF



6.5AQ36 Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Reverse stand-off voltage	V _{RWM}	I _R =1μA			36	V
Breakdown Voltage	V _{BR}	I _R =1mA	40	41.8		V
Reverse Leakage Current	I _{LEAK}	V _R =36V			1	μA
Clamp Voltage ¹	V _C	I _{PP} =1A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		45	52	V
		I _{PP} =5A, t _p =8/20μs, Pin 1 or Pin 2 to Pin 3		58.5	62	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Pin 1 or Pin 2 to Pin 3		0.65		Ω
Peak Pulse Current	I _{PP}	t _p =8/20μs			7	A
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz		45	50	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz		25	40	pF

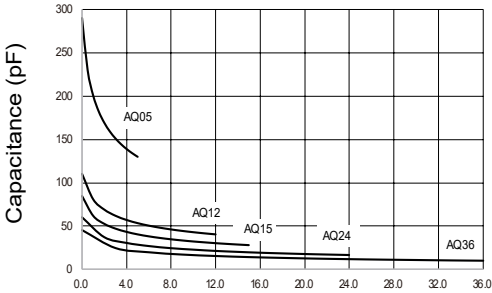
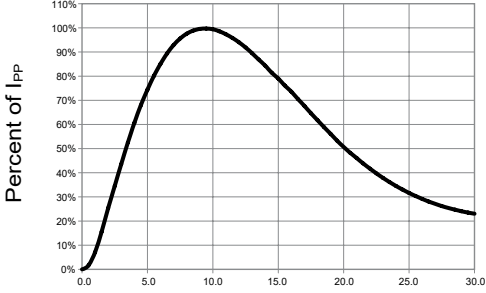
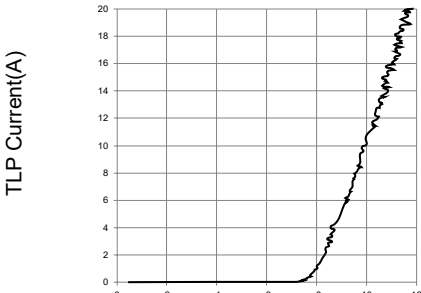
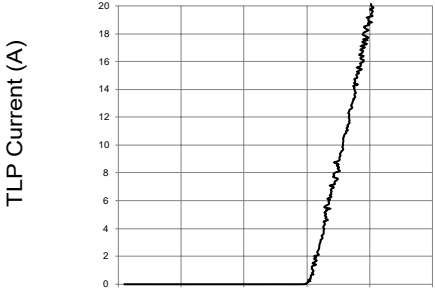
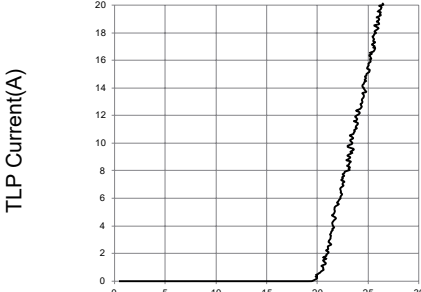
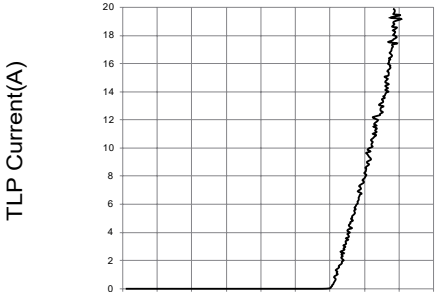
Note:

¹ Parameter is guaranteed by design and/or component characterization.

² Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2= 90ns

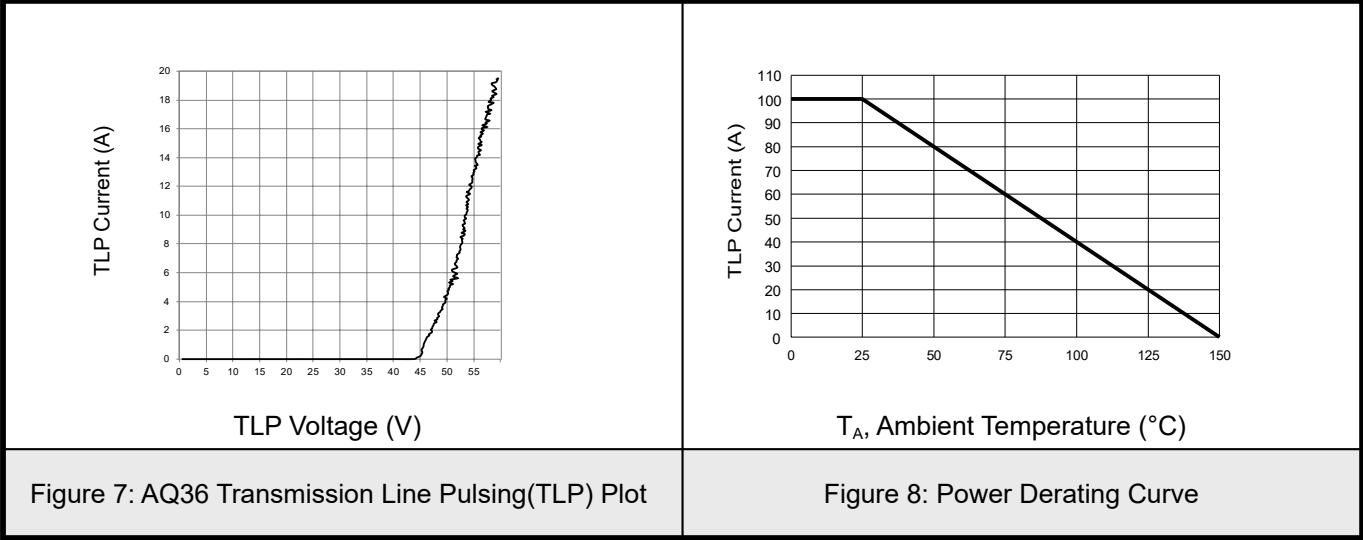


7.1Typical characteristic

 Capacitance (pF) Reverse Bias (V)	 Percent of I_{PP} Time (μs)
Figure 1: Capacitance vs. Reverse Bias (Pin1 or Pin2 to Pin3)	Figure 2: 8/20 μs Pulse Waveform
 TLP Current(A) TLP Voltage (V)	 TLP Current (A) TLP Volatge (V)
Figure 3: AQ05 Transmission Line Pulsing(TLP) Plot	Figure 4: AQ12 Transmission Line Pulsing(TLP) Plot
 TLP Current(A) TLP Voltage (V)	 TLP Current(A) TLP Voltage (V)
Figure 5: AQ15 Transmission Line Pulsing(TLP) Plot	Figure 6: AQ24 Transmission Line Pulsing(TLP) Plot



7.2Typical characteristic





7.3Typical characteristic



Figure 9: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at +8KV

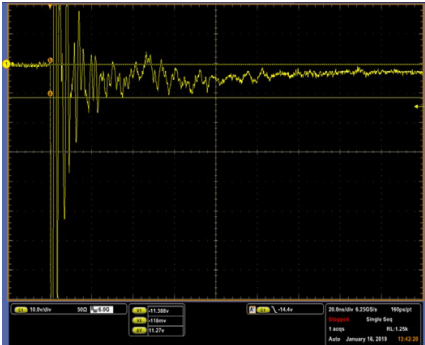


Figure 10: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at -8KV



Figure 11: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at +8KV



Figure 12: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at -8KV

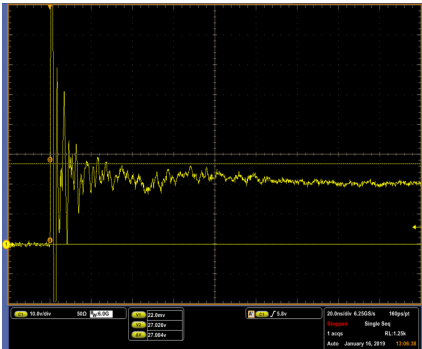


Figure 13: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at +8KV

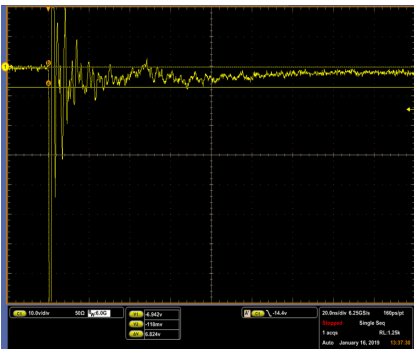


Figure 14: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at -8KV

7.4 Typical characteristic

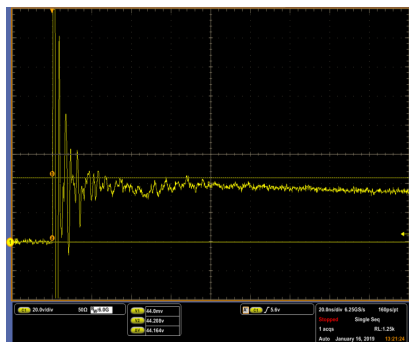


Figure 15: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at +8KV

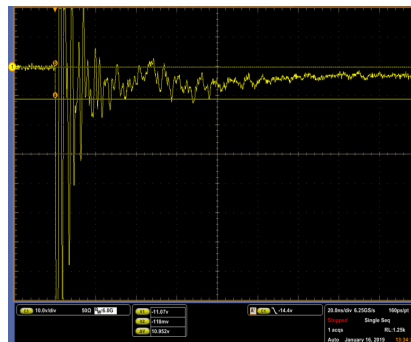


Figure 16: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at -8KV

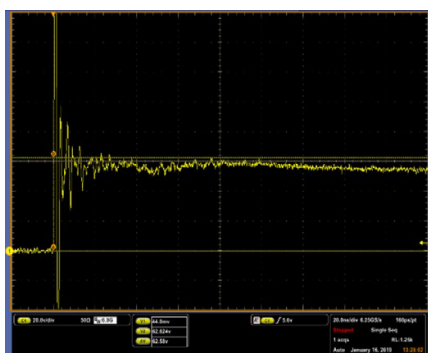


Figure 17: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at +8KV

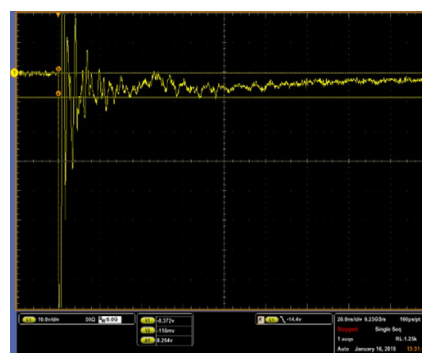
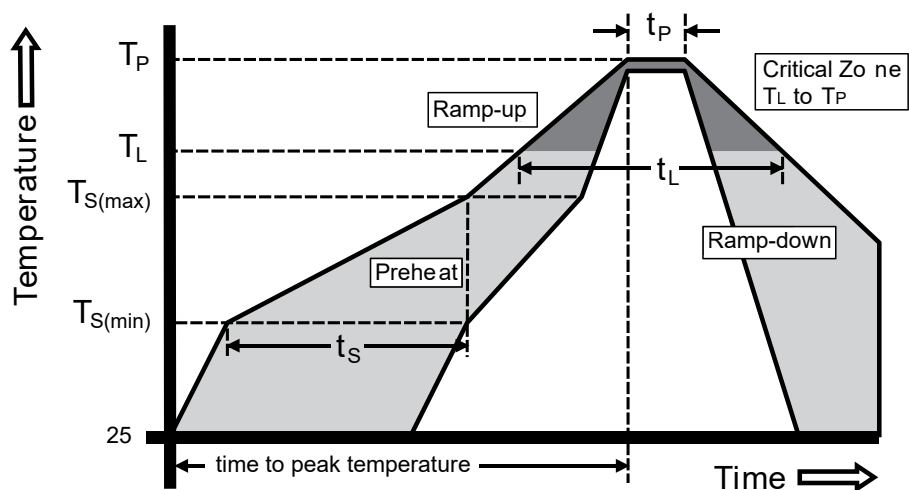


Figure 18: ISO10605 (C:330pF, R:330Ω)
contact discharge plot at -8KV



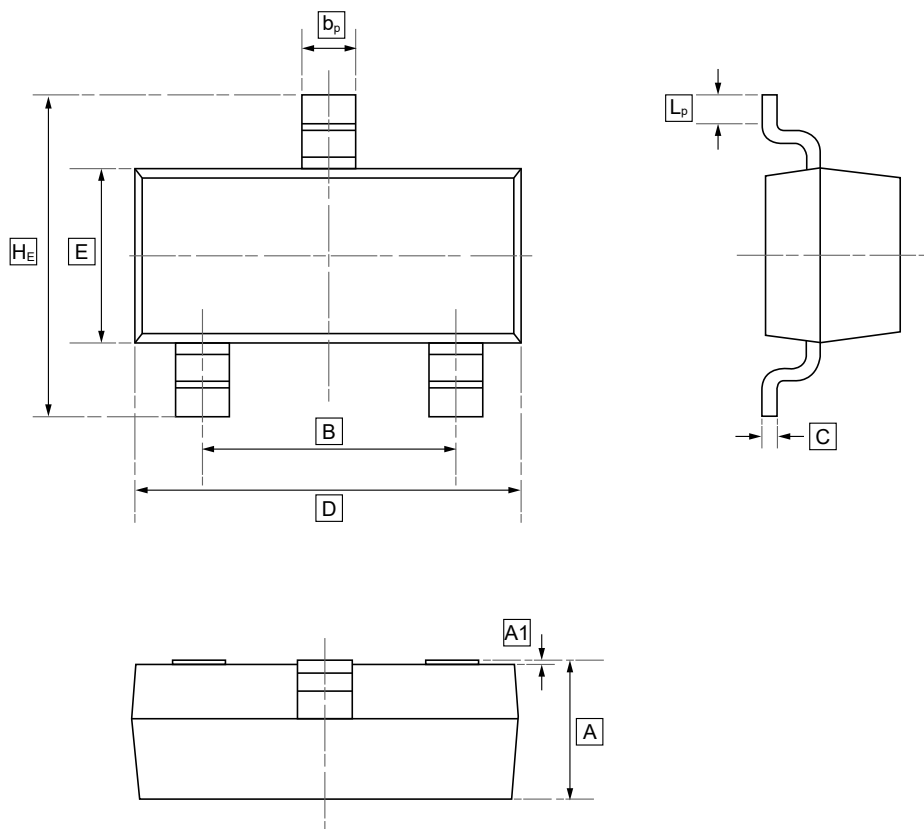
8. Soldering parameters

Reflow Condition		Pb-Free Assembly
Pre Heat	-Temperature Min ($T_{s(min)}$)	150°C
	-Temperature Max ($T_{s(max)}$)	200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	217°C
	-Temperature(T_L)	60-150 secs.
Peak Temp (T_p)		+260 $^{+0/-5}$ °C
Time within 5°C of actual Peak Temp (T_p)		20-40 seconds
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		260°C





9.SOT-23 Package Outline Dimensions

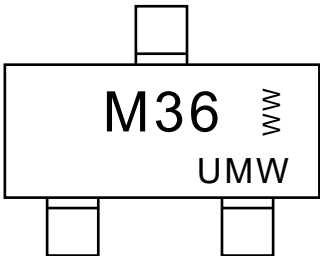


DIMENSIONS (mm are the original dimensions)

Symbol	A	B	b_p	C	D	E	H_E	A1	L_p
Min	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20
Max	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50



10.Ordering information



WW: Batch Code

Order Code	Package	Base QTY	Delivery Mode
UMW AQ36-02HTG	SOT-23	3000	Tape and reel



11.Disclaimer

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